

Abstract of the Disclosure

A bipolar transistor having a base semiconductor layer structure to minimize base parasitic resistance and a method of manufacturing the bipolar transistor are provided. In the provided bipolar transistor, a collector region of a second conductivity type, which is defined by isolation regions, is formed on a semiconductor substrate of a first conductivity type. A first base semiconductor layer of the first conductivity type extends from the upper surface of the collector region to the upper surface of the isolation regions. Here, the first base semiconductor layer is formed of a silicon germanium (SiGe) layer. Second base semiconductor layers of the first conductivity type are formed on the portions of the first base semiconductor layer except for the portions having the emitter region and the emitter insulating layers. Base ohmic layers are formed on the second base semiconductor layers.

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